PseudoGap Superconductivity near Localization Threshold

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Superconductivity v/s Localization

- Granular systems with Coulomb interaction
 K.Efetov 1980 et al *"Bosonic mechanism"*
- Coulomb-induced suppression of Tc in uniform films *"Fermionic mechanism"* A-Finkelstein 1987, et al
- <u>Competition of Cooper pairing and</u> <u>localization (no Coulomb)</u>

Imry-Strongin, **Ma-Lee**, Kotliar-Kapitulnik, Bulaevsky-Sadovsky(mid-80's) **Ghosal, Randeria, Trivedi 1998-2001**

There will be no grains and no Coulomb in this talk !

Plan of the talk

- 1. Motivation from experiments
- 2. BCS-like theory for critical eigenstates
 - transition temperature
 - local order parameter
- 3. Superconductivity with pseudogap
 - transition temperature v/s pseudogap
 - tunnelling conductance
 - spectral weight
- 4. Conclusions and open problems

Major exp. data calling for a new theory

Activated resistivity
 in insulating a-InO_x
 D.Shahar-Z.Ovadyahu 1992,
 V.Gantmakher et al 1996

 $T_0 = 3 - 15 K$

Local tunnelling data

B.Sacepe et al 2007-8

• Nernst effect above T_c P.Spathis, H.Aubin et al 2008







Class of relevant materials

- Amorphously disordered (no structural grains)
- Low carrier density

 (around 10²¹ cm⁻³ at low temp.)

 Examples:

InO_x NbN_x thick films or bulk (+ B-doped Diamond?) TiN thin films Be, Bi (ultra thin films)

Phase Diagram



Theoretical model

Simplest BCS attraction model, but for critical (or weakly) localized electrons

$$\mathbf{H} = \mathbf{H}_0 \quad - \quad \mathbf{g} \int d^3 \mathbf{r} \ \mathbf{\Psi}_{\uparrow}^{\dagger} \mathbf{\Psi}_{\downarrow}^{\dagger} \mathbf{\Psi}_{\downarrow} \mathbf{\Psi}_{\uparrow}$$

 $\Psi = \sum c_j \Psi_j (r)$ Basis of localized eigenfunctions

M. Ma and P. Lee (1985): S-I transition at $\delta_{I} \approx T_{c}$

<u>Superconductivity at the</u> <u>Localization Threshold:</u> $\delta_{L} \rightarrow 0$

Consider Fermi energy very close to the mobility edge:

single-electron states are extended but fractal and populate small fraction of the whole volume

How BCS theory should be modified to account for eigenstate's fractality ?

Method: combination of analitic theory and numerical data for Anderson mobility edge model

Mean-Field Eq. for T_c

$$\Delta(r) = \int K_T(r, r') \Delta(r') d^d r'$$
(9)

where kernel \hat{K}_T is equal to

$$K_T(r,r') = \frac{\lambda}{2\nu_0} \sum_{ij} \frac{\tanh\frac{\xi_i}{2T} + \tanh\frac{\xi_j}{2T}}{\xi_i + \xi_j} \psi_i(r)\psi_j(r)\psi_i(r')\psi_j(r')$$
(10)

Standard averaging over space $\Delta(r) \to \overline{\Delta}$ leads to "Anderson theorem" result: totally incorrect in the present situation.

The reason: critical eigenstates $\psi_j(r)$ are strongly correlated in real 3D space, they fill some small **submanifold** of the whole space only. In fact one should define T_c as the divergence temperature of the Cooper ladder

$$C = \left(1 - \hat{K}\right)^{-1}$$

Thus averaging procedure should be applied to \mathcal{C} instead of K

We expand C in powers of K and average over disorder realizations. Keeping main sequence of resulting diagramms only, we come to the following equation for determination of T_c :

$$\Phi(\xi) = \frac{\lambda}{2} \int \frac{d\xi' \tanh(\xi'/2T)}{\xi'} M(\xi - \xi') \Phi(\xi') \tag{11}$$

$$M(\omega) = \mathcal{V}\overline{M_{ij}} = \int \overline{\psi_i^2(r)\psi_j^2(r)} d^d r \quad \text{for} \quad |\xi_i - \xi_j| = \omega$$

For critical eigenstates

$$L_{\rm loc} \to \infty$$

one finds

 $\langle M_i \rangle \approx 3\ell^{-(d-d_2)} L^{-d_2}.$ $E_0 = 1/\nu_0 \ell^3$ $M(\omega) = \left(\frac{E_0}{\omega}\right)^{\gamma}$

where

$$\gamma = 1 - \frac{D_2}{d}$$

$$D_2 \approx 1.3$$
 in 3D

is a measure of fractality

Usual "dirty superconductor":

$$M(\omega) = 1 \qquad \gamma = 0$$

3D Anderson model: $\gamma = 0.57$



FIG. 2: (Color online) Correlation function $M(\omega)$ for 3DAM with Guassian disorder and lattice sizes L = 10, 14, 20 at the mobility edge E = 5.5 (red, blue and black points) and at the energy E = 8 inside localized band (green points). Inset shows γ values for L = 10.12.14.16.20.

Modified mean-field approximation for critical temperature T_c

$$\Delta(\xi) = \frac{\lambda}{2} \int d\zeta \eta(\zeta) M(\xi - \zeta) \Delta(\zeta)$$
$$\eta_i \equiv \eta_{ii} = \xi_i^{-1} \tanh(\xi_i/2T),$$
$$T = \frac{1}{2} \int d\zeta \eta(\zeta) M(\xi - \zeta) \Delta(\zeta)$$

$$T_c^0(\lambda,\gamma) = E_0 \lambda^{1/\gamma} C(\gamma)$$

For small λ this T_c is higher than BCS value !

arxiv:0810.2915 Y.Yanase & N.Yorozu: T_c for doped diamond, Si and SiC

Virial expansion method (A.Larkin & D.Khmelnitsky 1970)

$$F = \sum_{n=1}^{\infty} \mathcal{F}^{(n)} = \sum_{i} F_i + \sum_{i>j} (F_{ij} - F_i - F_j) \qquad V_{\Delta} = -\sum_{j} (\Delta S_j^+ + \Delta^* S_j^-)$$
$$+ \sum_{i>j>k} (F_{ijk} - F_{ij} - F_{jk} - F_{ik} + F_i + F_j + F_k) + \dots$$
$$\chi(T) = -\frac{\partial^2 F}{\partial \Delta \partial \Delta^*} = \sum_{M=1} \chi_M(T)$$

T_c from 3 different calculations



Order parameter in real space

$$\tilde{\Delta}(\mathbf{r}) = \frac{g}{2} \sum_{k} \Delta_{k} \eta_{k} \psi_{k}^{2}(\mathbf{r})$$
$$\eta_{i} \equiv \eta_{ii} = \xi_{i}^{-1} \tanh(\xi_{i}/2T); \quad \Delta_{k} \Longrightarrow \Delta(\xi) \quad \text{for } \xi = \xi_{k}$$

$$\overline{(\tilde{\Delta}(\mathbf{r}))^2} \equiv \frac{1}{\mathcal{V}} \int d^d \mathbf{r} \tilde{\Delta}^2(\mathbf{r}) = \lambda \int_0^\infty d\xi \eta(\xi) \Delta_c^2(\xi)$$

$$\overline{\tilde{\Delta}(\mathbf{r})} \equiv \frac{1}{\mathcal{V}} \int d^d \mathbf{r} \tilde{\Delta}(\mathbf{r}) = \lambda \int_0^\infty d\xi \eta(\xi) \Delta_c(\xi)$$

Fluctuations of SC order parameter With Prob = p << 1 $\Delta(\mathbf{r}) = \Delta$, otherwise $\Delta(\mathbf{r}) = 0$ \Longrightarrow SC fraction = $\frac{\left(\tilde{\Delta}(\mathbf{r})\right)^2}{(\tilde{\Delta}(\mathbf{r}))^2} = \lambda Q(\gamma) = \frac{Q(\gamma)}{C^{\gamma}(\gamma)} \left(\frac{T_c}{E_0}\right)^{\gamma} \ll 1$

prefactor ≈ 1.7 for $\gamma = 0.57$

Higher moments:
$$\frac{\left(\tilde{\Delta}(\mathbf{r})\right)^n}{(\tilde{\Delta}(\mathbf{r}))^n} \propto (T_c/E_0)^{(1-d_n/d)(n-1)}$$

$$\langle P_q \rangle \sim \ell^{-(d-d_q)(q-1)} L^{-d_q(q-1)} \propto L^{-d_q(q-1)}$$

Tunnelling DoS



Neglected : off-diagonal terms

$$M_{ijkl} = \int d\mathbf{r} \psi_i^*(\mathbf{r}) \psi_j^*(\mathbf{r}) \psi_k(\mathbf{r}) \psi_l(\mathbf{r}) \,,$$

Non-pair-wise terms with 3 or 4 different eigenstates were omitted

To estimate the accuracy we derived effective Ginzburg-Landau functional taking these terms into account

 $F[\Psi(\mathbf{r})]$ defined in terms of an envelope function

$$\begin{split} \Psi(\mathbf{r}) &= \Delta(\mathbf{r}) / \tilde{\Delta}(\mathbf{r}) & \tilde{\Delta}(\mathbf{r}) = \frac{g}{2} \sum_{k} \Delta_{k} \eta_{k} \psi_{k}^{2}(\mathbf{r}) \\ F_{GL}[\Psi(\mathbf{r})] &= \nu_{0} T_{c}^{2} \int d\mathbf{r} \left(a(\mathbf{r}) \Psi^{2}(\mathbf{r}) + \frac{b}{2} \Psi^{4}(\mathbf{r}) + C |\nabla \Psi(\mathbf{r})|^{2} \right) \\ \text{Gi} &\sim \frac{b^{2}}{C^{3} (\nu_{0} T_{c})^{2}} \sim 1 & \text{Gi}_{d} \sim \frac{W^{2}}{C^{3}} \sim 1 \end{split}$$

Superconductivity at the Mobility Edge: major features

- Critical temperature $T_{\rm c}$ is well-defined through the whole system in spite of strong $\Delta(r)$ fluctuations
- Local DoS strongly fluctuates in real space; it results in asymmetric tunnel conductance
 G(V,r) ≠ G(-V,r)
- Both thermal (Gi) and mesoscopic (Gi_d) fluctuational parameters of the GL functional are of order unity

Superconductivity with Pseudogap

Now we move Fermi-level into the range of localized eigenstates

Local pairing in addition to collective pairing

Local pairing energy

Parity gap in ultrasmall grains
 K. Matveev and A. Larkin 1997



$$\Delta_P = \frac{1}{2}\lambda\delta \qquad \qquad \lambda_R = \lambda/(1 - \lambda\log(\epsilon_0/\delta)). \qquad \Delta_P = \frac{\delta}{2\ln\frac{\delta}{\Delta}}$$

c

2. Parity gap for Andersonlocalized eigenstates

The increase of thermodynamic potential Ω due to addition of *odd* electron to the ground-state is

$$\delta\Omega_{\text{oe}} = \xi_{m+1} = \xi_{m+1} - \tilde{\xi}_{m+1} + \tilde{\xi}_{m+1} = \frac{g}{2}M_{m+1} + O(\mathcal{V}^{-1})$$

$$\tilde{\xi}_j = \xi_j - \frac{g}{2}M_j.$$

Energy of two single-particle excitations after depairing:

$$2\Delta_P = \xi_{m+1} - \xi_m + gM_m = \frac{g}{2}(M_m + M_{m+1}) + O(\mathcal{V}^{-1})$$

$$\langle M_i \rangle = 3\ell^{-(d-d_2)} L_{\rm loc}^{-d_2}, \qquad \Delta_P = \frac{3}{2}g\ell^{-3}(L_{loc}/\ell)^{-d_2} = \frac{3\lambda}{2}E_0 \left(\frac{E_c - E_F}{E_0}\right)^{\nu d_2}$$

P(M) distribution



Activation energy T_I from Shahar-Ovadyahu exp. and fit to theory



The fit was obtained with single fitting parameter $A \approx 0.5 \lambda E_0$

Example of consistent choice:

$$\lambda_{\cdot}$$
 = 0.05 E_{0} = 400 K

Critical temperature in the pseudogap regime

MFA:

$$\Delta(\xi) = \frac{\lambda}{2} \int d\zeta \eta(\zeta) M(\xi - \zeta) \Delta(\zeta)$$

$$\eta_i \equiv \eta_{ii} = \xi_i^{-1} \tanh(\xi_i/2T).$$

Here we use $M(\omega)$ specific for localized states

MFA is OK as long as
$$Z\sim
u_0 T_c L^d_{loc}$$
 is large

Correlation function $M(\omega)$



No saturation at $\omega < \delta_L$: $M(\omega) \sim \ln^2 (\delta_L / \omega)$ (Cuevas & Kravtsov PRB,2007)

Superconductivity with $Tc < \delta_L$ is possible

This region was not found previously

Here "local gap" exceeds SC gap :

$$\Delta_P = \frac{1}{2D^{\gamma}(\gamma)} \delta_L \left(\frac{\Delta(0)}{\delta_L}\right)^{\gamma}$$

FIG. 2: (Color online) Correlation function $M(\omega)$ for 3DAM with Guassian disorder and lattice sizes L = 10, 14, 20 at the mobility edge E = 5.5 (red, blue and black points) and at the energy E = 8 inside localized band (green points). Inset shows γ values for L = 10.12.14.16.20.

Critical temperature in the pseudogap regime

$$\Delta(\xi) = \frac{\lambda}{2} \int d\zeta \eta(\zeta) M(\xi - \zeta) \Delta(\zeta)$$

$$\eta_i \equiv \eta_{ii} = \xi_i^{-1} \tanh(\xi_i/2T).$$

We need to estimate

MFA:

$$Z \sim \nu_0 T_c L^d_{loc}$$

$$R_{\omega} \approx 2L_{\rm loc} \ln \frac{\delta_L}{\omega} \gg L_{\rm loc} \qquad R_0^2$$

$$R_0^2 = \frac{\sum_{ij} r_{ij}^2 M_{ij}}{\sum_{ij} M_{ij}}$$

$$Z_{\rm eff} \equiv \nu_0 T_c R_0^3 = 8 \frac{T_c}{\delta_L} \ln^3 \frac{\delta_L}{T_c} \quad \begin{array}{lt is nearly constant in a \\ \mbox{very broad range of } \frac{\delta_L}{T_c} \end{array}$$



FIG. 25: (Color online) Virial expansion results for T_c (red points) and typical pseudogap Δ_P (black) as functions of E_F . The model with fixed value of the attraction coupling constant g = 1.7 was used; pairing susceptibilities were calculated using equations derived in Appendix B.

FIG. 26: (Color online) Virial results for T_c (red points), typical pseudogap Δ_P (black) and the corresponding level spacing δ_L (green), as functions of E_F on semi-logarithmic scale.

Transition exists even at $\delta_L >> T_{c0}$

Single-electron states suppressed by pseudogap

Pseudo spin" representation:

$$S_{\mu}^{+} = a_{\mu\tau}^{+} a_{\mu\tau}^{+}$$
 $S_{\mu}^{-} = a_{\mu\tau}a_{\mu\tau}$
 $2S_{\mu}^{+} = a_{\mu\tau}^{+} a_{\mu\tau}^{+}$ $S_{\mu}^{-} = a_{\mu\tau}a_{\mu\tau}$
 $2S_{\mu}^{+} = a_{\mu\tau}^{+} a_{\mu\tau}^{+} + a_{\mu\tau}^{+} a_{\mu\tau}$
 H_{Brs} acts on Even sector: $\overline{M}_{\mu\nu} = \frac{1}{\sqrt{V}} M(\overline{s}_{\mu} - \overline{s}_{\nu})$
all states which are $D_{ost}^{-} = \frac{1}{\sqrt{V}} M(\overline{s}_{\mu} - \overline{s}_{\nu})$
 $2- filled or empty$

"Pseudospin" approximation

 $Z \sim \nu_0 T_c L_{loc}^d$

Effective number of interacting neighbours

Third Scenario

- Bosonic mechanism: preformed Cooper pairs + competition Josephson v/s Coulomb – SIT in arrays
- Fermionic mechanism: suppressed Cooper attraction, no paring – S M T
- Pseudospin mechanism: individually localized pairs
 SIT in amorphous media

SIT occurs at small Z and lead to paired insulator

$$H = 2\sum_{i} \xi_{i} s_{i}^{z} - \sum_{ij} M_{ij} (s_{i}^{x} s_{j}^{x} + s_{i}^{y} s_{j}^{y})$$

How to describe this quantum phase transition ? Cayley tree model is solved (L.loffe & M.Mezard)

Strong local pseudogap above T_c: experiment B.Sacepe et al



At T=Tc - almost fully developed gap but no coherence peak

Point-contact spectroscopy

Generalization of the Blonder-Tinkham-Klapwijk formula for pseudogaped SC

1e transport: $eV_c = \Delta_P + \Delta$

2e transport: $2eV_c = 2\Delta$



Scales as $(G_t)^2$

Scales as G_t

unvisible in tunnelling regime $G_t \ll 1$

Double-peak structure at moderate G_t

Full Spectral Weight K(T)

$$K^{tot}(T) = \frac{2}{\pi} \int_0^{\Omega_{max}} \Re \sigma(\omega, T) d\omega + \rho_s(T) \equiv K(T) + \rho_s(T)$$

is usually (BCS) const across Tc : contributions from superconductive response and from DoS suppression cancel each other. It is NOT the case for underdoped HTSC :

Experiment: D.Basov et al 1994 Theory: L.loffe & A.Millis 1999

The same effect is even more pronounced in Pseudogaped SC:



Qualitative features of "Pseudogaped Superconductivity":

- STM DoS evolution with T
- Double-peak structure in point-contact conuctance
- Nonconservation of full spectral weight across T_c

S-I transition on Cayley tree



example with branching number q = 3

$$H = 2\sum_{i} \xi_i s_i^z - \sum_{ij} M_{ij} (s_i^x s_j^x + s_i^y s_j^y)$$

Eq.(1) contains random energies ξ_i ⁽¹⁾ Large bandwidth W

 $M_{ij} = M$ for nearest neighbours

Full self-consistent equation can be written for distribution functions of local fields Δ_i

Control parameter: g = qM/W



Conclusions

Pairing on nearly-critical states produces fractal superconductivity with relatively high T_c but very small superconductive density

Pairing of electrons on localized states leads to hard gap and Arrhenius resistivity for 1e transport

Pseudogap behaviour is generic near S-I transition, with "insulating gap" above T_c

New type of S-I phase transition is described (on Cayley tree, at least)

Major unsolved problems (theor)

- 1. How to include magnetic field into the "fractal" scheme ?
- 2. Transition between pseudogap SC and insulator. Why Cooper pair transport is activated ?
- 3. Rectangular gap in local tunnelling ?
- 4. Size-dependence of SIT (Kowal-Ovadyahu 2007)

Coulomb enchancement near mobility edge ??

Normally, Coulomb interaction is overscreened, with universal effective coupling constant ~ 1 Condition of universal screening: $2\sigma/(T_c\kappa) \sim (\xi_0/a_{\rm scr})^2/\kappa \gg 1$ $a_{\rm scr}$ is the Thomas-Fermi screening length. $\sigma = (e^2 k_F / 6\pi^2) (k_F l)$ Example of $a-InO_x$ bad dirty metal with $k_F l \sim 0.3$ the ratio $\sigma/T_c \sim 10$ $e^2k_F \sim 5000K$ dielectric constant $\kappa \geq 30$ Effective Couloomb potential is weak:

 $\mu \sim 2\sigma/(T_c\kappa) < 1$



No way to describe InO_x data by Gaussian fluctuations contrary to NbSi case: M.Serbyn et al, Phys.Rev.Lett. 102, 067001 (2009) K.Michaeli and A.Finkelstein arxiv:0902.2732

"Phase fluctuations"? Where the amplitude comes from?